

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (Ultra High speed U-MOSIII)

TPCP8003-H

High Efficiency DC/DC Converter Applications

Notebook PC Applications

Portable Equipment Applications

Unit: mm

- Small footprint due to a small and thin package
- High speed switching
- Small gate charge: $Q_{SW} = 7.5 \text{ nC (typ.)}$
- Low drain-source ON-resistance: $R_{DS(ON)} = 130 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 5.4 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A (max)} \text{ (} V_{DS} = 100\text{V)}$
- Enhancement mode: $V_{th} = 1.1 \text{ to } 2.3 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 1\text{mA)}$

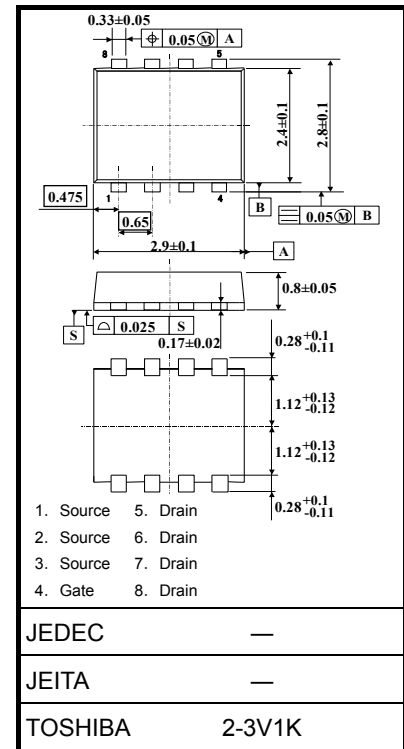
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	100	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	100	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	2.2	A
	Pulsed (Note 1)	I_{DP}	8.8	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2a)		P_D	1.68	W
Drain power dissipation ($t = 5 \text{ s}$) (Note 2b)		P_D	0.84	W
Single-pulse avalanche energy (Note 3)		E_{AS}	3.93	mJ
Avalanche current		I_{AR}	2.2	A
Repetitive avalanche energy ($T_c = 25^\circ\text{C}$) (Note 4)		E_{AR}	0.016	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 4, refer to the next page.

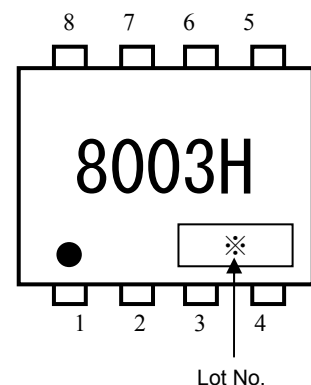
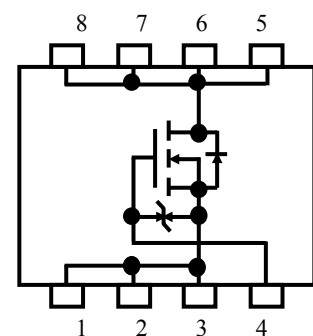
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.017 g (typ.)

Circuit Configuration

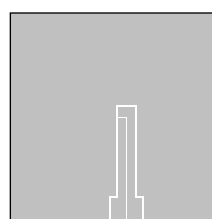


Thermal Characteristics

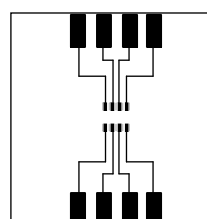
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	$R_{th(ch-a)}$	74.4	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	$R_{th(ch-a)}$	148.8	°C/W

Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)

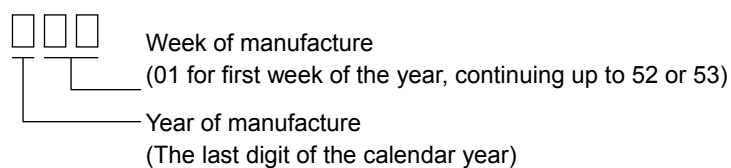


(b)

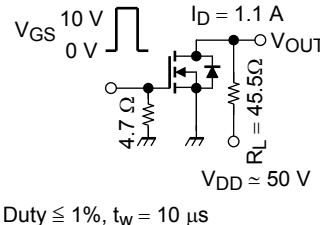
Note 3: $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1\text{ mH}$, $R_G = 1\ \Omega$, $I_{AR} = 2.2\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: * Weekly code: (Three digits)

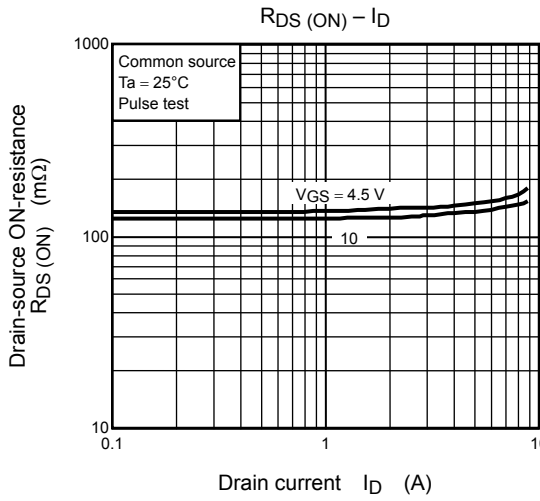
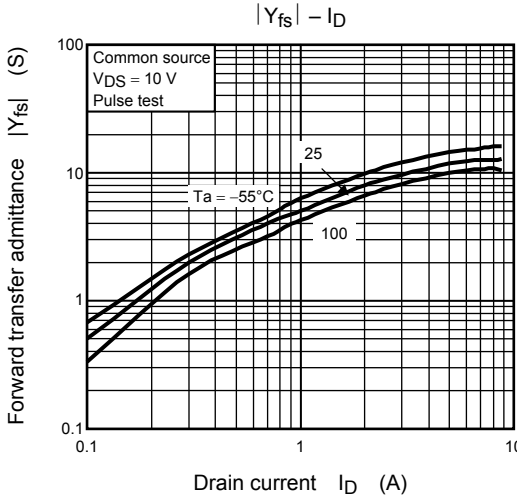
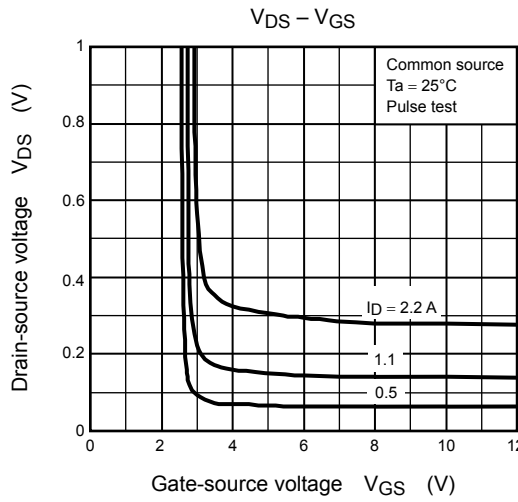
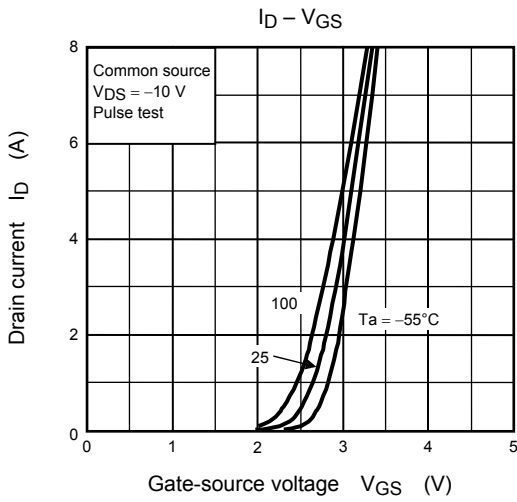
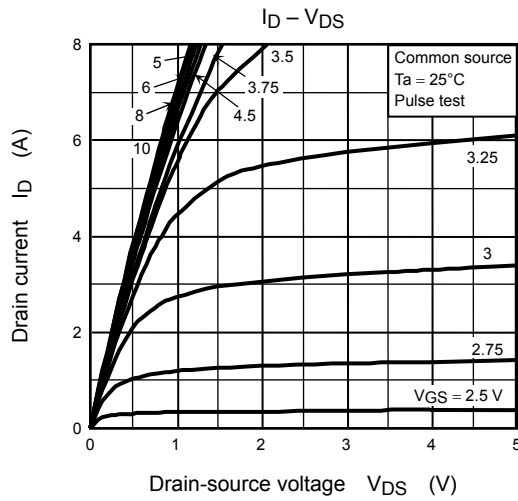
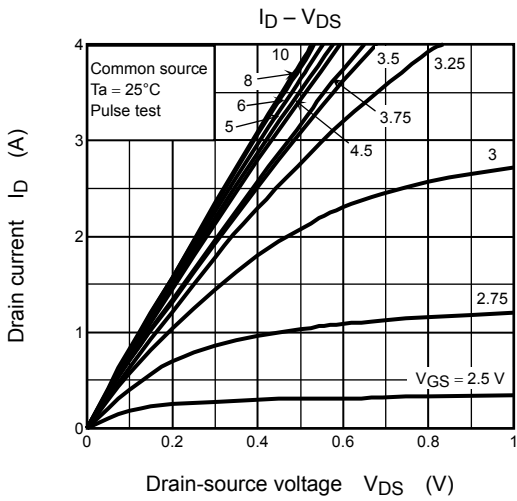


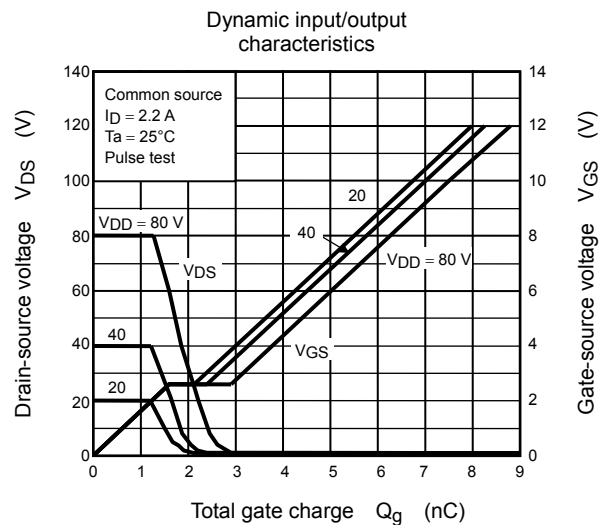
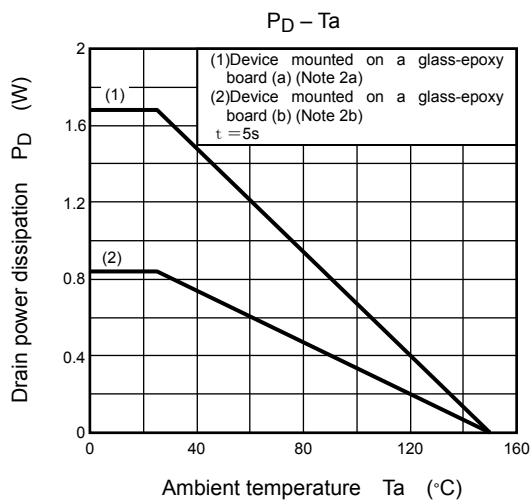
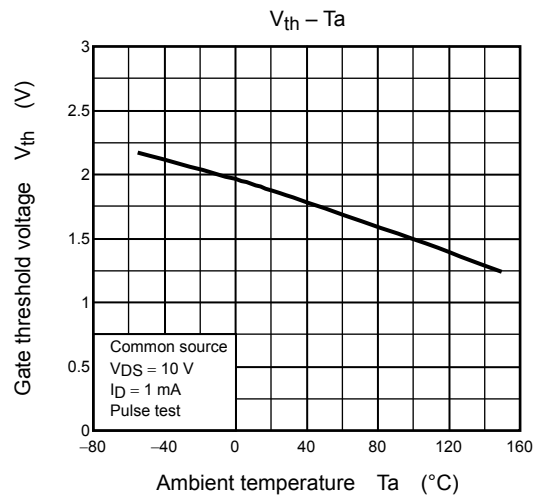
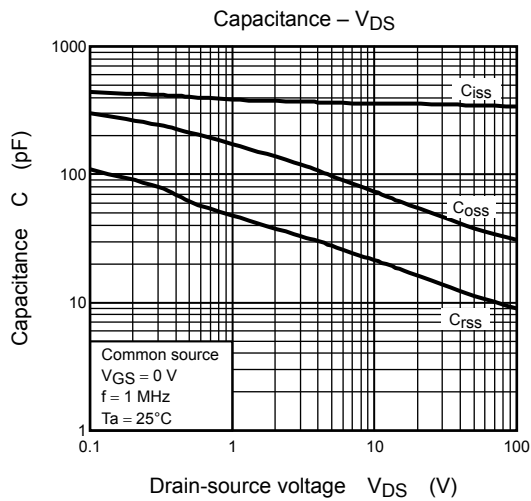
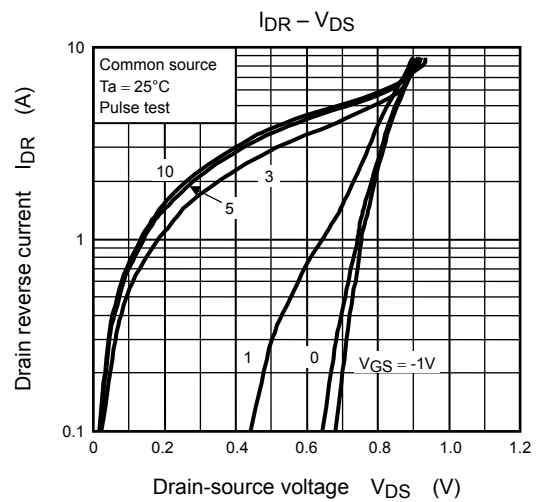
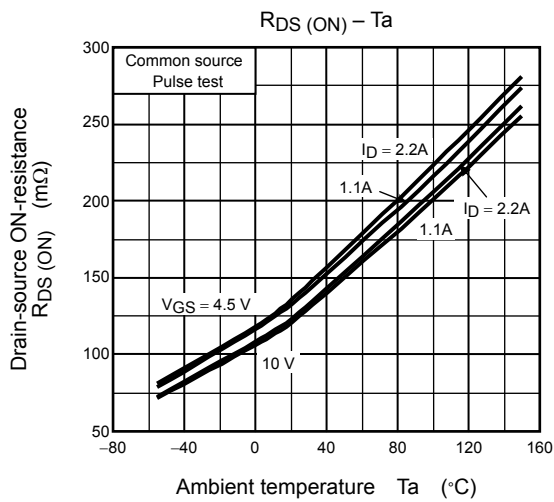
Electrical Characteristics (Ta = 25°C)

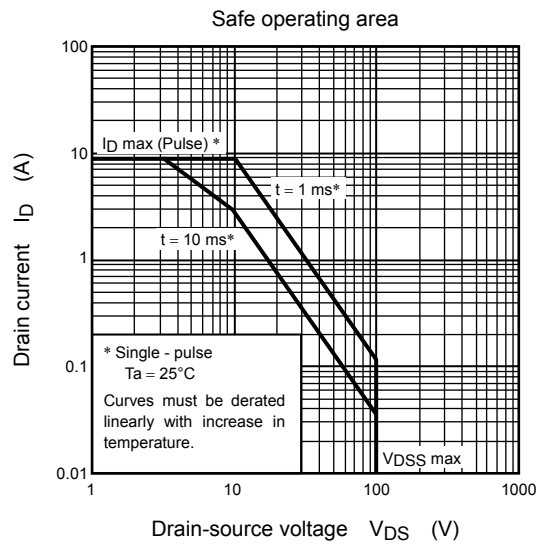
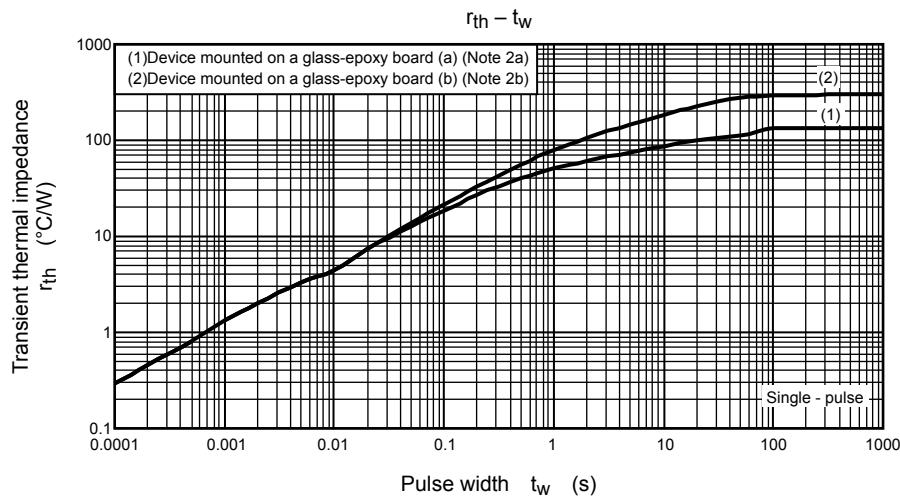
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	—	—	10	μA
Drain-source breakdown voltage		V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	100	—	—	V
		V _(BR) DSX	I _D = 10 mA, V _{GS} = -20 V	60	—	—	
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.1	—	2.3	V
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 4.5 V, I _D = 1.1 A	—	140	190	mΩ
			V _{GS} = 10 V, I _D = 1.1 A	—	130	180	
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 1.1 A	2.7	5.4	—	S
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	360	—	pF
Reverse transfer capacitance		C _{rss}		—	22	—	
Output capacitance		C _{oss}		—	75	—	
Switching time	Rise time	t _r		—	7	—	ns
	Turn-on time	t _{on}		—	14	—	
	Fall time	t _f		—	3	—	
	Turn-off time	t _{off}		—	17	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ 80 V, V _{GS} = 10 V, I _D = 2.2 A	—	7.5	—	nC
			V _{DD} ≈ 80 V, V _{GS} = 5 V, I _D = 2.2 A	—	4.5	—	
Gate-source charge 1		Q _{gs1}	V _{DD} ≈ 80 V, V _{GS} = 10 V, I _D = 2.2 A	—	1.6	—	
Gate-drain (“Miller”) charge		Q _{gd}		—	1.3	—	
Gate switch charge		Q _{SW}		—	2.0	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	8.8	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 2.2 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V







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